

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
a capacitor structure formed above the semiconductor substrate and comprising:
 - a first electrode,
 - a second electrode provided below the first electrode,
 - a third electrode provided below the second electrode,
 - a first dielectric film provided between the first electrode and the second electrode, and
 - a second dielectric film provided between the second electrode and the third electrode;
 - an insulating film covering the capacitor structure and having a first hole reaching the first electrode, a second hole reaching the second electrode, and a third hole reaching the third electrode;
 - a first conductive connection electrically connecting the first electrode and the third electrode and having portions buried in the first and third holes; and
 - a second conductive connection formed separately from the first conductive connection and having a portion buried in the second hole,wherein an outer end of the second electrode is entirely positioned outside the first electrode in a direction parallel to a main surface of the semiconductor substrate,
and

an outer end of the third electrode is entirely positioned outside the second electrode in the direction parallel to the main surface of the semiconductor substrate.

2. (Cancelled)
3. (Original) The semiconductor device according to claim 1, further comprising a ring-shape electrode surrounding the first electrode.
4. (Currently Amended) The semiconductor device according to claim 3, wherein an outer end of the first dielectric film and [an] the outer end of the second electrode are aligned with an outer end of the ring-shape electrode.
5. (Currently Amended) The semiconductor device according to claim 4, wherein [an] the outer end of the third electrode is aligned with an outer end of the second dielectric film.
6. (Original) The semiconductor device according to claim 1, wherein the first, second, and third electrodes are formed of the same material.
7. (Original) The semiconductor device according to claim 1, wherein the first, second, and third electrodes are formed of the same material.
8. (Withdrawn) The semiconductor device according to claim 1, wherein the capacitor structure further comprises a fourth electrode provided below the third electrode and a third dielectric film provided between the third electrode and fourth

electrode; the insulating film further has a fourth hole reaching the fourth electrode; and the second conductive connection further has a portion buried in the fourth hole.

9. (Withdrawn) The semiconductor device according to claim 8, wherein the capacitor structure further comprises a fifth electrode provided below the fourth electrode and a fourth dielectric film provided between the fourth electrode and fifth electrode; the insulating film further has a fifth hole reaching the fifth electrode, and the first conductive connection further has a portion buried in the fifth hole.

10. (Original) The semiconductor device according to claim 1, further comprising a wiring metal layer provided between the semiconductor substrate and the capacitor structure.

11. (Withdrawn) A method of manufacturing a semiconductor device, comprising:

forming a stacked film above a semiconductor substrate, the stacked film comprising a first conductive film, a second conductive film provided below the first conductive film, a third conductive film provided below the second conductive film, a first dielectric film provided between the first conductive film and the second conductive film, and a second dielectric film provided between the second conductive film and third conductive film;

forming a capacitor structure comprising a first electrode formed of the first conductive film, a second electrode formed of the second conductive film, and a third electrode formed of the third conductive film by patterning the stacked film;

forming an insulating film covering the capacitor structure and having a first hole reaching the first electrode, a second hole reaching the second electrode and a third hole reaching the third electrode; and

forming a first conductive connection electrically connecting the first electrode and the third electrode and having portions buried in the first and third holes, and a second conductive connection formed separately from the first conductive connection and having a portion buried in the second hole.

12. (Withdrawn) The method according to claim 11, wherein forming the capacitor structure comprises:

patterning the first conductive film to form the first electrode and a ring-shape conductive portion surrounding the first electrode;

forming a mask pattern covering the first electrode and a part of the ring-shape conductive portion;

patterning the first dielectric film with the ring-shape conductive portion and the mask pattern used as a mask;

patterning the ring-shape conductive portion with the mask pattern used as a mask to form a ring-shape electrode; and

patterning the second conductive film with the patterned first dielectric film used as a mask.

13. (Withdrawn) The method according to claim 12, wherein forming the capacitor structure further comprises:

further patterning the patterned first dielectric film with the mask pattern used as a mask;

patterning the second dielectric film with the patterned second conductive film used as a mask;

further patterning the patterned second conductive film with the mask pattern used as a mask to form a second electrode; and

patterning the third conductive film with the patterned second dielectric film used as a mask to form a third electrode.

14. (Withdrawn) The method according to claim 11, wherein the first, second and third electrodes are formed of the same material.

15. (Withdrawn) The method according to claim 11, wherein the first and second dielectric films are formed of the same material.